L Number	Hits	Search Text	DB	Time stamp
1	1	"6710391"	USPAT; US-PGPUB;	2004/07/09 10:58
2	1	"20040000686"	EPO; JPO; IBM_TDB USPAT; US-PGPUB;	2004/07/09 10:59
4	202	houston-theodore-w.in.	EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/09 10:59
5	21	houston-theodore-w.in. and DRAM and capacitor and ground	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/09 10:59
6	19	(houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/09 10:59
7	5	((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/07/09 10:59
8	5	((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/07/09 10:59
9	2	(("20010030338" "20020020883" "20020064065 and DRAM and ground	"\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	"200044/10175/1019" 6235603" "625 11:00
3	8	("20010030338" "20020020883" "20020064065"	US-PGPUB; EPO; JPO;	6220044/1057'/10'96235603" "6255 11:08
10	660	DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/09 11:09
11	406	((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:11
12	400	gate ((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:35
13	386		USPAT;	2004/07/09
		DRAMeandtrapaoitomsandt@foundthandtch\$4 omerhmdv&f)pandep&anasid&planadidat&foth andhoubsonath&ododeswuine and BRAMnandd gapacinot 4nd7&fodhd) 20004me6666667 bouston+thendop&awainz\$5)	US-PGPUB; EPO; JPO; IBM_TDB	11:17
		(%0080000000000000000000000000000000000		
		capacitor and ground) and (method or process)) (((houston-theodore-w.in. and		

DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and

7.4			1	1 000 1 100 100
14	3	(((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4	USPAT; US-PGPUB;	2004/07/09
		or remov\$4) and planari\$6)) and (trench	EPO; JPO;	
		and substrate) and source and drain and	IBM TDB	
		gate) not ("6710391" "20040000686"	15155	
		houston-theodore-w.in.		
		(houston-theodore-w.in. and DRAM and		·
		capacitor and ground)		
		((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
15	383	DRAM (BRAMcapdcyroundndndroupdciand and	USPAT;	2004/07/09
		(mdfhddcoriprocesnswland4plwnahizat6h\$4	US-PGPUB;	11:15
		φr (hemetφa) theddplenwria6) andnBRAMrendh	EPO; JPO;	
		enpasubetrand) gandndøuand amethodinrand pabeesnøt andfombanatics 20040000686"	IBM_TDB	
		Modes Shop	5"1"6060351'	11"6204115"1"62356h3"1"6
		and DRAM and	7 (0000331	1 0204113 1 0233003 1 0
		¢4paentenasgrandgrandron20883" "20020064065	"1"6060351"1	"6204115" "623560B" "62
		and DRAM and	'	, , , ,
		capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
		(((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) and planariz\$5)	- " - " - 0 - 0 - 5 - 1 - 1	1, 1, 6, 2, 6, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1,
		((("20010030338" "20020020883" "2002006406 and DRAM and ground)	5 1 6060321	1 6204115 62356µ3 6
		(("20010030338" "20020020883" "20020064065	" "6060351"	"6204115"L"623560B"L"62
		and (contact)) not (((DRAM and ground	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	3233335 32
		and capacitor and ((dielectric or		
16	383	insulabram winding tennisandreapmovser and	USPAT;	2004/07/09
		planerecticand insahehsahdwithsteath\$4	US-PGPUB;	11:15
		emdremov¢é) andddphanamid6gatendn¢trench	EPO; JPO;	
		456710B911ate208460866868 and drain and	IBM_TDB	
		hatetonothe86316391In. "20040000686"		
		hhousonnthheddogewwimm. and DRAM and		
		<pre>¢hpusion=theddgreuwdin. and DRAM and ¢aheuston=theodppundlin. and DRAM and</pre>		
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		DRAMeand) capabitotoendhgodomd waind. and		
		WRAMheddorapzoress) andngrphadarazet\$5)		
		(mehbodton-pheodese) wand. pandaDRAMtand		
		¢aphoustonathlegeorady.and amethRaMoand	i	
		papeessor and granadizand (method or	L	l
		process100and3prahas020020883" "2002006406		
		444"DRAMO8BG39854HZ0020020883" "2002006406		
		4x42pbam0and3gr4uadp20020883" "20020064065 4x42q0an0a08384j"pnnza0xp\$8an4"2mezno44065	11.6060351	6204115 6235605 62
		amdcesentact)) not (((DRAM and ground	1 6060331 1	0204113 0233605 02
		and capacitor and ((dielectric or		
l	-	insulat\$4) with (etch\$4 or remov\$4) and	1	
		planari\$6)) and (trench and substrate)		
		and source and drain and gate) not		
		("6710391" "20040000686"		
		houston-theodore-w.in.		
		(houston-theodore-w.in. and DRAM and		
		capacitor and ground)		
		((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
		(((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) and planariz\$5)	•	
		((("20010030338" "20020020883" "2002006406	5" "6060351'	' "6204115" "6235603" "6
		and DRAM and ground)		W.CO.O.A.G. G.C
		(("20010030338" "20020020883" "20020064065		"6204115" "6235603" "62
earch His	story 7	and (contact adj pillar))) and (method or process)		
	-	process; and (method of process)		

			·	
17	131	((((((DRAM and ground and capacitor and	USPAT;	2004/07/09
		((dielectric or insulat\$4) with (etch\$4	US-PGPUB;	11:17
		or remov\$4) and planari\$6)) and (trench	EPO; JPO;	
	ĺ	and substrate) and source and drain and	IBM_TDB	
		gate) not ("6710391" "20040000686"	_	
		houston-theodore-w.in.		į
1		(houston-theodore-w.in. and DRAM and		
ł		capacitor and ground)		
1		((houston-theodore-w.in. and DRAM and		
1		capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
		(((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) and planariz\$5)		
1		((("20010030338" "20020020883" "2002006406	5"1"6060351"	1 " 62 0 4 1 1 5 " 1 " 62 3 5 6 b 3 " 1 " 62
		and DRAM and ground)		,,
		(("20010030338" "20020020883" "20020064065	"1"6060351"1	"6204115" "623560B" "625
		and (contact)) not (((DRAM and ground	, 000000	, 0201220
		and capacitor and ((dielectric or		
		insulat\$4) with (etch\$4 or remov\$4) and		
18	82	plamarispramand(ground and supatrate) and	USPAT;	2004/07/09
10	"-	4ndiebacteiendrdininland4gawethnoetch\$4	US-PGPUB;	11:19
ì		φr6rem39\$4) ä2dOpDenenes6868)) and (trench	EPO; JPO;	11.13
	ľ	hndssubstheodorend.inurce and drain and	IBM TDB	
	}	dhoastnotthe66do0894"in"28040DBAM86nd	15.1_155	
		henaconothendousewadh.		
		(hhousonnthheddogeewwiin.anddDRAMMandd		
		capacitor and ground) and (method or		
		prhoussph-thehduseow-theodudeDRAMnandnd		
		DRAMcandrcapdcgroundhdagdowmdthaddor		
	1	pmethed) pr(pfhoessph-ahdopbanawizat\$ahd		
	•	関係AMoundonapheodoreawdiground) DRAM and		
		¢mpahodhuonaphewuoleawulgloanu,bahu anu ¢mpahodoorapdogeonhd)anddplmnahodab\$5)		
		proheustonandepdemerwzsh) and DRAM and		
		¢4p4200000303039r4uad0240308808th82002006406	5"1"6060351"	1"6204115"1"6235603"1"62
ŀ		pmdcBBAM) anddgpbandriz\$5)	0000331	0204113 0233003 02
į		(('\'200000000388'\'\'200000000883\'\'\'200000066065	RTTRAGGGGGGTT	T # # # # # # # # # # # # # # # # # # #
		and DRAMtand gdoupdllar))) and (method or	011000003411	0224113770223305377022
İ		pt8288300383838 (he200200209838 e4820020665	"1"6060351"1	"6204115" "6235603" "625
		<pre>andcondnadct(dinbectfictBaminadlgrocad)</pre>	1 0000331 1	0201113 0233005 023
		and capacitor and ((dielectric or		
		insulat\$4) with (etch\$4 or remov\$4) and		
19	69	plamaria & DRAMmandtgenuhdanddsubpacater	USPAT;	2004/07/09
10		and \$\die\estdidreiniandlga\(\frac{4}{2}\) woth	US-PGPUB;	11:19
1		(867h0396r remova008666planari\$6)) and	EPO; JPO;	
		horench-shedodobetwain) and source and	IBM TDB	
		dhemntendtheodornew.in67and9DRAM and	1511_155	
	i	Capaendoned housedn-theodore-w.in.		
		(Mbossonthheddogeewwimn.anddDRAMMandd		
		capacitor and ground) and (method or		
		prhoussph-thehduseow-theododeDRAMnandnd		
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		pmethod) pr (prhoussph-ahdophanawizat\$and		·
		DRAMoundonapheodoreawdiground) DRAM and		
	1	dapahodoorapdogeenhd) anddplanahodat\$5)		
		proheustonandepdemerwzsh) and DRAM and		
		¢4p42000000a0a39r4u00020000800800000000000000000000000000	5" "6060351"	l "6204115" l "62356h3" l "62
		pmdcBBAM) anddqpbandriz\$5)	[, 0000001	2237273 3233373 32
		(("200000000388" 20000000883" 2000006 0 05	87786666857	TRE004155TTEE25EE93TTEE5
		and DRAMtand gdoundllar))) and (method or	[
	1	pt32003000300000000000000000000000000000	.	"6204115" "623560B" "625
		dedcondnadit (diebectii CDBAMiandlgrotad))	' ' ' '	
		and ¢apacondradid(didlecerricoror		
		insulat\$44) wiwhtheteh\$4\$6roremem\$4\$4ahd		· ·
		planari\$6)) and (trench and substrate)		
	I	and source and drain and gate) not		

and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in.

(houston-theodore-w.in. and DRAM and

20		IIIIIIIII AND and around and somesition	IICDATT.	2004/07/09
20	66	<pre>((((((((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with</pre>	USPAT; US-PGPUB;	11:19
		(etch\$4 or remov\$4) and planari\$6)) and	EPO; JPO;	*****
		(trench and substrate) and source and	IBM TDB	
		drain and gate) not ("6710391"	_	
		"20040000686" houston-theodore-w.in.		
		(houston-theodore-w.in. and DRAM and		
ŀ		<pre>capacitor and ground) ((houston-theodore-w.in. and DRAM and</pre>		
		capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		,
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
		(((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) and planariz\$5)		
		((("20010030338" "20020020883" "2002006406	5" "6060351" 	"6204115" "62356D3" "6
		and DRAM and ground) (("20010030338" "20020020883" "20020064065	 	"6204115" "623560B" "62
		and (contact)) not (((DRAM and ground	1 6060331 1	0204113 0233005 02
		and capacitor and ((dielectric or		
		insulat\$4) with (etch\$4 or remov\$4) and		
		planari\$6)) and (trench and substrate)		
21	60	4ή¢(\$φ¢¢¢¢(BRAMdæadingændngaaa) nepacitor	USPAT;	2004/07/09
		and710d9&Tect20040000686Tat\$4) with	US-PGPUB;	11:20
		Metsh\$4-bheodmov\$\(\psi\) iand planari\(\psi\) and	EPO; JPO;	
	i	(høunthnahleodbstrutéh.anddsDRAMeandd dapaniand gndegrnund("6710391"	IBM_TDB	
		"2004800068KëodometwminheeddrBRAMiand		
		¢hpusionthudgreuwdinandn¢mBRAMdand		
		papaesspr andhgmound) theodore-w.in. and		
		DRAMusidnespeodore-undingranddDRAMdand		
		¢mpahodoorapdogeomhd) anddplmnahodao\$5)		
		probenston (thhoderenwthnodend-DRAM. andd		
		DRAMCandrcapdcgroundhdagdoumdthaddor pmethod)prapdop&anariana)planarizat\$5)		
		(((Nanatanaoneanariana)pianarizata) (((Nanatanaoneanariana)pianarizata)	 5" "6060351"	
		andaDRAMranddggggundd) and (method or	0000331	0201113 0233 013 0
		pt820030030030030000000000000000000000000	" "6060351"	"6204115" "623560B" "62
		4nd"200m0ec03a6f p2DDa00208abd 'ae02066606	b" "6060351'	"6204115" "62356þ3" "6
		pmdcBBAM) anddgfmandod or process)) and		
		(\$2000000000000000000000000000000000000	" " 6060351"	"6204115" "623560β" "62
		and (¢entend) adjot(dielebRamcand ground		
		andutapa¢1tprwand (édth\$écoricemov\$4))) andulsap4¢iwothwiehchp1aos osmov\$4) and		
		plenarod6)))andd(expnsA4and substrate)		
22	5	4ή¢(\$φψτ¢¢(4DEAMramd gmdugdtehdnoapacitor	USPAT;	2004/07/09
		4H671Qd9&Tect20046000f86Tat\$4) with	US-PGPUB;	11:40
		Metsh\$4-theremov\$4) iand planari\$6)) and	EPO; JPO;	
		(hounthnahleadbserwten.anddsDRAMeandd	IBM_TDB	
		dapaniand gadegrnond("6710391" "2004860068KëodonetwninheeddrBRAMiand	İ	
		<pre>thous tone the ddground in an and make the ddground in an /pre>		
		papaesispr andhomenmithendere-w.in. and		
		DRAMusidnesheodbos-widingrenddDRAMdand		
		¢mpahodoorapdogeenhd) anddp(mnahodat\$5)		
		prohenston (theoderenwth modernd-DRAM. and d		
		DRAMcandrcandcgroundhdandowmdtheddor		
	:	wmethed) prapdophanarizat\$5)	F # 1 # CO CO 2 F 1 I	1, 11, 12, 12, 13, 14, 14, 12, 12, 12, 12, 14, 14, 14, 14, 14, 14, 14, 14, 14, 14
		(((H@Q@t0030B080442002002086d"DRAM02066406	 5" "6060351'	"6204115" "62356 3" "6
		(((Magston30Bs6dor2se22n20aAd"pRAM0and6406 sapabRAMranddggsondd) and (method or		
		(((M@Q8t0n30R86dotr20020n20and"pRAMO2nd6406 captaDrAMranddgggoundd) and (method or processon3and8planap20920883" "20020064065	 " "6060351"	 "6204115" "6235603" "62
		((代的公民主的30日86日中下2002的120名日日 PRAMO21116406 由中国的主义 Carter (Method or private 150020064065	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6
		(((Magston30Bs6dor2ec2nn20and"pramoand6406 sapabkamranddggmondd) and (method or process)93and8plaman20939883" "20020064065 4nd"20010a003adj p2nnam92988ad "medbod6406 pndcBBAM)anddgrmanddo or process)) and (\$82000000d933dIeI20020020883h\$UI0029064965	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6
		(((Magston30Bs6dor2ec2nn20and"pRAMOand6406 sapaDRAMranddgggondd) and (method or process) and (method or process) and (method or process) and (secondoad3ad] process) and (secondoad3ad1er2ec2ncess) and (secondoad3ad1er2ec2ncess) and (secondoad3ad1er2ec2ncess) and	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6
		(((Magston30Bs6dor2sp2nn20and"pRAMOand6406 sapabkAmranddgggondd) and (method or process) and (method or process) and (method or process) and (secondoad3ad] process) and (secondoad3ad] process) and (secondoad3ad1e120020020883H\$U18020054065 and (centend) adjotdie1ebkAmcand ground andutapac1torwand (edch3ecoricemov\$4)))	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6
		(((Magston30Bs6dor2sp2nn20and"pRAMOand6406 sapabkAmranddgggondd) and (method or process) and (method or process) and (method or process) and (secondoad3ad] process) and (secondoad3ad] process) and (secondoad3ad1e120020020883H\$U18020064065 and (centend) adjotdielebkAmcand ground andutapac1torwand (edch3ecoricemov\$4))) andulssp4ciworhwiehchplabs osmov\$4) and	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6
		(((Magston30Bs6dor2sp2nn20and"pRAMOand6406 sapabkAmranddgggondd) and (method or process) and (method or process) and (method or process) and (secondoad3ad] process) and (secondoad3ad] process) and (secondoad3ad1e120020020883H\$U18020054065 and (centend) adjotdie1ebkAmcand ground andutapac1torwand (edch3ecoricemov\$4)))	 " "6060351" 5" "6060351' 	"6204115" "6235603" "62 "6204115" "6235603" "6

23	0	20040012022.URPN.	USPAT	2004/07/09 11:21	
24	1	"6562679".PN.	USPAT	2004/07/09 11:25	
25	0	6727542.URPN.	USPAT	2004/07/09 11:25	
26	9	("4864374" "5229326" "5998225" "6236079" "6297525" "6329684" "6352896" "6436762" "6555891").PN.	USPAT	2004/07/09 11:26	
27	0	6746915.URPN.	USPAT	2004/07/09	
28	0	6746915.URPN.	USPAT	2004/07/09	
29	55	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:31	
		(("20010030338" "20020020883" "2002006406 and DRAM and ground) (("20010030338" "20020020883" "20020064065 and (contact)) not (((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) ((("20010030338" "20020020883" "2002006406	" "6060351"	"6204115" "6235603" '	'625 ·
		and DRAM and ground) (("20010030338" "20020020883" "20020064065 and (contact adj pillar))) and (method or process)) and (method or process)) and (second adj (dielectric or insulati\$4))) and ((second adj (dielectric or insulati\$4))) and (capacitor with (plate or electrode))) and expos\$4) and (expos\$4			
30	3	with (etch\$4 or remov\$4))) not méméty(ámd(¢ápBAmtemdagdoundnamat adj päpäertosmandgfødmaladfripleteinsulat\$4) wiehtfedeh\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/07/09 11:34	
31	10	and (trench and substrace) and source and drayadad"gatë,045899"67103915248" "36096060686"65603561-the68066416"in. "Kans66a"the866561695n #6629882"and capas285r and company of the substrace o	USPAT	2004/07/09 11:33	
32	0	(2002:000:000:000:000:000:000:000:000:00	USPAT	2004/07/09 11:34	٠

	334	plug) and (ground adj (plate or electrode))	US-PGPUB; EPO; JPO;	11:35	
34	526	(IBM_TDB USPAT;	2004/07/09	
		plug) and (ground adj (plate or electrode))) not ("6710391"	US-PGPUB; EPO; JPO;	11:36	
		"20040000686" houston-theodore-w.in.	IBM_TDB		
		(houston-theodore-w.in. and DRAM and capacitor and ground)			
		((houston-theodore-w.in. and DRAM and			
		capacitor and ground) and (method or			
		process)) (((houston-theodore-w.in. and			
		DRAM and capacitor and ground) and (method or process)) and planarizat\$5)			
		(((houston-theodore-w.in. and DRAM and			
		capacitor and ground) and (method or			
		process))	5" "6060351"	 "6204115" "62356) 03" "62
		and DRAM and ground)			
ı		(("20010030338" "20020020883" "20020064065	" "6060351"	"6204115" "623560	B" "625
		((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4			
		or remov\$4) and planari\$6)) and (trench			
		and substrate) and source and drain and			,
		gate) not ("6710391" "20040000686" houston-theodore-w.in.			
		(houston-theodore-w.in. and DRAM and			
		capacitor and ground)			
		((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or			
		process)) (((houston-theodore-w.in. and			
		DRAM and capacitor and ground) and			
		(method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and			
		capacitor and ground) and (method or			
		process))	 5" "6060351'	 "6204115" "62356	
		and DRAM and ground) (("20010030338" "20020020883" "20020064065	 060351"	 "6204115" "623560	 B" "625
		and (contact adj pillar))			
		<pre>((((((((((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with</pre>			
		(etch\$4 or remov\$4) and planari\$6)) and			
		(trench and substrate) and source and			
		drain and gate) not ("6710391" "20040000686" houston-theodore-w.in.			
		(houston-theodore-w.in. and DRAM and			,
		capacitor and ground)	<u> </u>	<u> </u>	l
		((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or			
		process)) (((houston-theodore-w.in. and			
		DRAM and capacitor and ground) and (method or process)) and planarizat\$5)			
		(((houston-theodore-w.in. and DRAM and			
		capacitor and ground) and (method or			
		<pre>process)) and planariz\$5) ((("20010030338" "20020020883" "2002006406</pre>	5"1"6060351'	' "6204115" "62356	03"1"62
		and DRAM and ground)			
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		and capacitor and ((dielectric or			
		<pre>insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate)</pre>			
		and source and drain and gate) not			
		("6710391" "20040000686"			
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		capacitor and ground)			
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534 memory and capacitor and (contact or

capacitor and ground) and (method or process)) (((houston-theodore-w.in. and 7/5/AM and capacitor and ground) and (method or process)) and planarizat\$5)

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((houston-theodore-w.in. and DRAM and

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                    ((memory and capacitor and (contact or
                                                               USPAT;
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                                                               US-PGPUB;
                   plug) and (ground adj (plate or
                                                                           11:36
                    electrode))) not ("6710391"
                                                               EPO; JPO;
                    "20040000686" houston-theodore-w.in.
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                    (houston-theodore-w.in. and DRAM and
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                    capacitor and ground) and (method or
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                    DRAM and capacitor and ground) and
                    (method or process)) and planarizat$5)
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                    capacitor and ground) and (method or
                   process)) and planariz$5)
                    ((("20010030338"|"20020020883"|"20020064065"|"6060351"||"6204115"|"62356b3"|"62
                    and DRAM and ground)
                    (("20010030338"|"20020020883"|"20020064065|"|"6060351"|"6204115"|"623560B"|"625
                    ((((DRAM and ground and capacitor and
                    ((dielectric or insulat$4) with (etch$4
                    or remov$4) and planari$6)) and (trench
                    and substrate) and source and drain and
                    gate) not ("6710391" "20040000686"
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                    capacitor and ground) and (method or
                   process)) (((houston-theodore-w.in. and
                    DRAM and capacitor and ground) and
                    (method or process)) and planarizat$5)
                    (((houston-theodore-w.in. and DRAM and
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                   process)) and planariz$5)
                    ((("20010030338"|"20020020883"|"2002006406$"|"6060351'||"6204115"|"62356b3"|"62
                    and DRAM and ground)
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                    and (contact adj pillar))
                    ((((((((((((DRAM and ground and capacitor
                    and ((dielectric or insulat$4) with
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                    capacitor and ground)
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                    capacitor and ground) and (method or
                   process)) (((houston-theodore-w.in. and
                    DRAM and capacitor and ground) and
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                    capacitor and ground) and (method or
                   process)) and planariz$5)
                    ((("20010030338"|"20020020883"|"20020064065"|"6060351"|"6204115"|"6235603"|"62
                    and DRAM and ground)
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                    and (contact)) not (((DRAM and ground
                    and capacitor and ((dielectric or
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                    process)) (((houston-theodore-w.in. and
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                  Search History
                    ((("20010030338"|"20020020883"|"20020064065"|"6060351"|"6204115"|"6235603"|"62
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36	40		USPAT;	2004/07/09
		plug) and (ground adj (plate or electrode))) not ("6710391"	US-PGPUB; EPO; JPO;	11:37
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		((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
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		capacitor and ground) and (method or		
		process))	 	1 "6204115"1"6235603"1"6
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		((((DRAM and ground and capacitor and	0000331	0204113 0233005 02
		((dielectric or insulat\$4) with (etch\$4		
		or remov\$4) and planari\$6)) and (trench		
		and substrate) and source and drain and		
		gate) not ("6710391" "20040000686"		
		houston-theodore-w.in.		
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		capacitor and ground)		
		((houston-theodore-w.in. and DRAM and		
		capacitor and ground) and (method or		
		process)) (((houston-theodore-w.in. and		
		DRAM and capacitor and ground) and		
		(method or process)) and planarizat\$5)		
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		capacitor and ground) and (method or		
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	•	((("20010030338" "20020020883" "2002006406	5"1"6060351'	l "6204115" l "62356b3" l "6
		and DRAM and ground)	, 3333337	
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	1	and (contact adj pillar))	, , ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
		((((((((((DRAM and ground and capacitor		
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	ļ.	"20040000686" houston-theodore-w.in.		
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37	5	capacitor (antiRamound) gandndmethodapacitor	USPAT;	2004/07/09
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